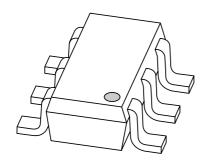
DISCRETE SEMICONDUCTORS

DATA SHEET



BC807DS PNP general purpose double transistor

Product specification Supersedes data of 2002 Aug 09 2002 Nov 22





PNP general purpose double transistor

BC807DS

FEATURES

- High current (500 mA)
- 600 mW total power dissipation
- Replaces two SOT23 packaged transistors on same PCB area.

APPLICATIONS

- · General purpose switching and amplification
- · Push-pull amplifiers
- Multi-phase stepper motor drivers.

DESCRIPTION

PNP transistor pair in a SOT457 (SC-74) plastic package.

MARKING

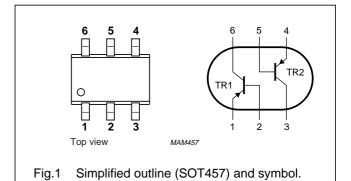
TYPE NUMBER	MARKING CODE
BC807DS	N2

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	-45	V
I _C	collector current (DC)	-500	mA
I _{CM}	peak collector current	-1	Α

PINNING

PIN	DESCRIPTION	
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
6, 3	collector	TR1; TR2



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per transis	Per transistor unless otherwise specified						
V _{CBO}	collector-base voltage	open emitter	_	-50	V		
V_{CEO}	collector-emitter voltage	open base	_	-45	V		
V _{EBO}	emitter-base voltage	open collector	_	- 5	V		
I _C	collector current (DC)		<u> </u>	-500	mA		
I _{CM}	peak collector current		Ī-	-1	Α		
I _{BM}	peak base current		_	-200	mA		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	<u> </u>	370	mW		
T _{stg}	storage temperature		-65	+150	°C		
Tj	junction temperature		<u> </u>	150	°C		
T _{amb}	operating ambient temperature		-65	+150	°C		
Per device	Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	600	mW		

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

PNP general purpose double transistor

BC807DS

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	note 1	208	K/W
	ambient			

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

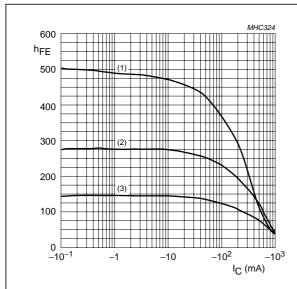
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	stor		•			
I _{CBO}	collector-base cut-off current	$V_{CB} = -20 \text{ V}; I_E = 0$	_	_	-100	nA
		V _{CB} = −20 V; I _E = 0; T _j = 150 °C	_	_	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h _{FE}	DC current gain	$V_{CE} = -1 \text{ V; } I_{C} = -100 \text{ mA; note 1}$	160	_	400	
		$V_{CE} = -1 \text{ V; } I_{C} = -500 \text{ mA; note 1}$	40	_	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}; \text{ note 1}$	_	_	-700	mV
V _{BE}	base-emitter voltage	$V_{CE} = -1 \text{ V; } I_{C} = -500 \text{ mA;}$ notes 1 and 2	_	_	-1.2	V
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	9	_	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V; } I_{C} = -10 \text{ mA;}$ f = 100 MHz	80	_	_	MHz

Notes

- 1. Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$
- 2. V_{BE} decreases by approximately -2 mV/K with increasing temperature.

PNP general purpose double transistor

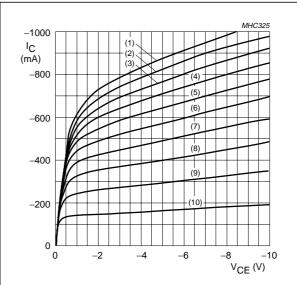
BC807DS



 $V_{CE} = 1 V.$

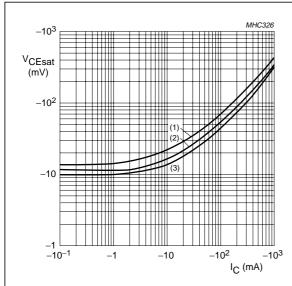
- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.2 DC current gain as a function of collector current; typical values.



- (1) $I_B = -7 \text{ mA}$.
- (5) $I_B = -4.2 \text{ mA}.$ (6) $I_B = -3.5 \text{ mA}.$
- (9) $I_B = -1.4 \text{ mA}.$ (10) $I_B = -0.7 \text{ mA}.$
- (2) $I_B = -6.3 \text{ mA}.$
- (6) $I_B = -3.5 \text{ mA}$. (7) $I_B = -2.8 \text{ mA}$.
- (3) $I_B = -5.6 \text{ mA}.$ (4) $I_B = -4.9 \text{ mA}.$
- (8) $I_B = -2.1 \text{ mA}.$

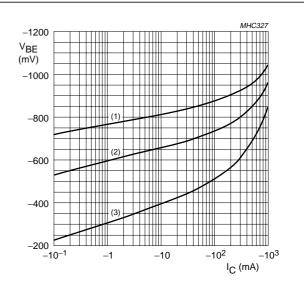
Fig.3 Collector current as a function of collector-emitter voltage; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $V_{CE} = 1 V$.

- (1) $T_{amb} = -55 \,^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.5 Base-emitter voltage as a function of collector current; typical values.

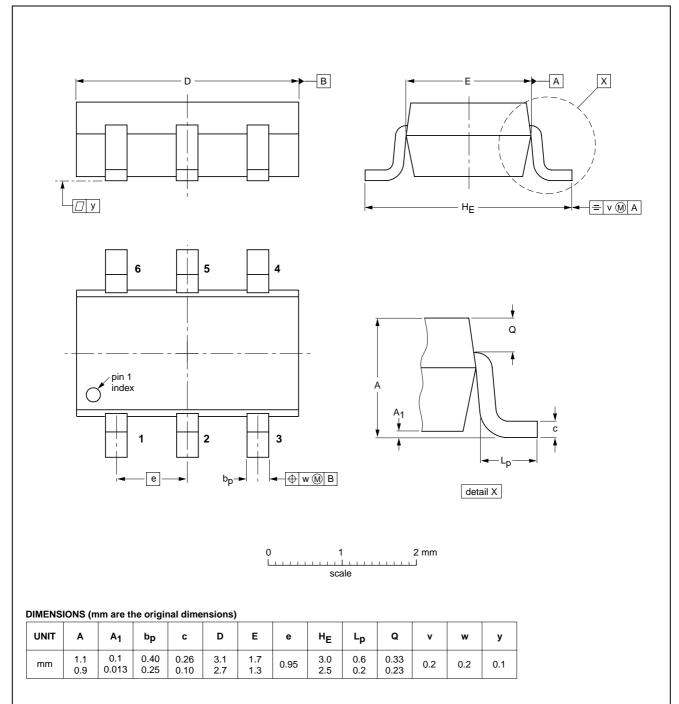
PNP general purpose double transistor

BC807DS

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



REFERENCES

EIAJ

SC-74

JEDEC

EUROPEAN

PROJECTION

ISSUE DATE

97-02-28

01-05-04

2002 Nov 22	5

IEC

OUTLINE VERSION

SOT457

PNP general purpose double transistor

BC807DS

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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PNP general purpose double transistor

BC807DS

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